

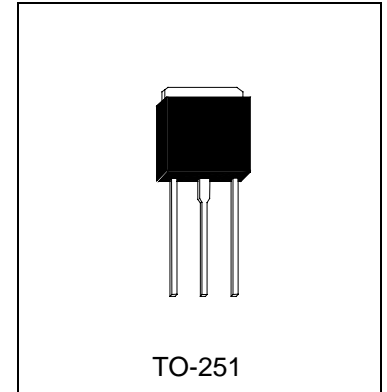


HI669A

NPN EPITAXIAL PLANAR TRANSISTOR

Description

The HI669A is designed for low frequency power amplifier.



Absolute Maximum Ratings (Ta=25°C)

- Maximum Temperatures
 - Storage Temperature -55 ~ +150 °C
 - Junction Temperature +150 °C
- Maximum Power Dissipation
 - Total Power Dissipation (Tc=25°C) 1 W
- Maximum Voltages and Currents
 - BVCBO Collector to Base Voltage 180 V
 - BVCEO Collector to Emitter Voltage 160 V
 - BVEBO Emitter to Base Voltage 5 V
 - IC Collector Current 1.5 A

Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	180	-	-	V	IC=1mA
BVCEO	160	-	-	V	IC=10mA
BVEBO	5	-	-	V	IC=1mA
ICBO	-	-	10	uA	VCB=160V
*VCE(sat)	-	-	1	V	IC=500mA, IB=50mA
*VBE(on)	-	-	1.5	V	VCE=5V, IC=150mA
*hFE1	60	-	200		VCE=5V, IC=150mA
*hFE2	30	-	-		VCE=5V, IC=500mA
fT	-	140	-	MHz	VCE=5V, IC=500mA
Cob	-	14	-	pF	VCB=10V, f=1MHz, IE=0

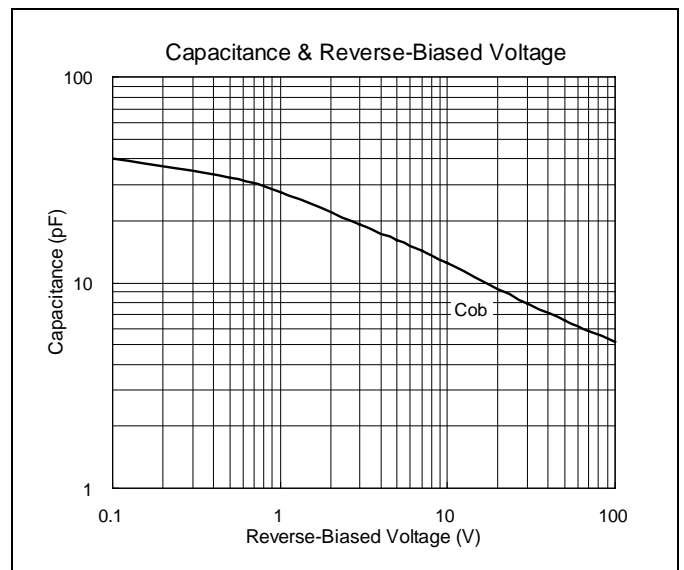
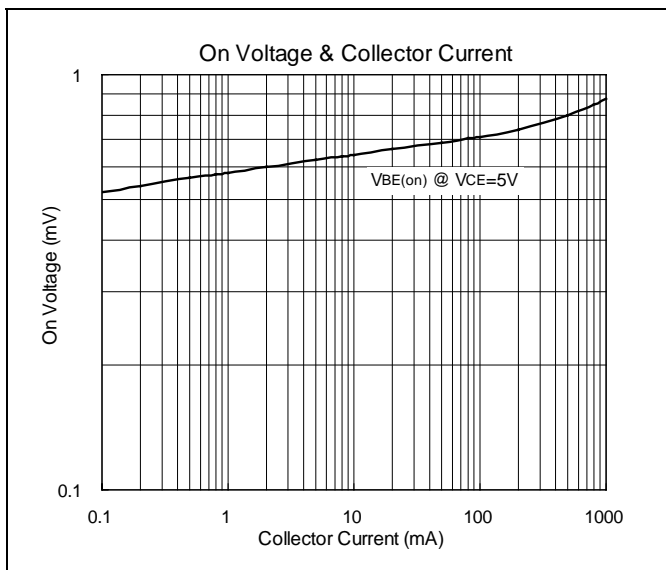
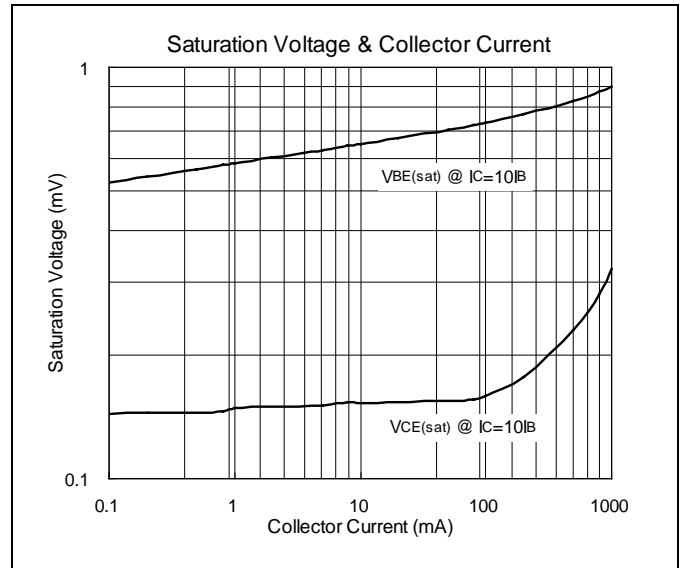
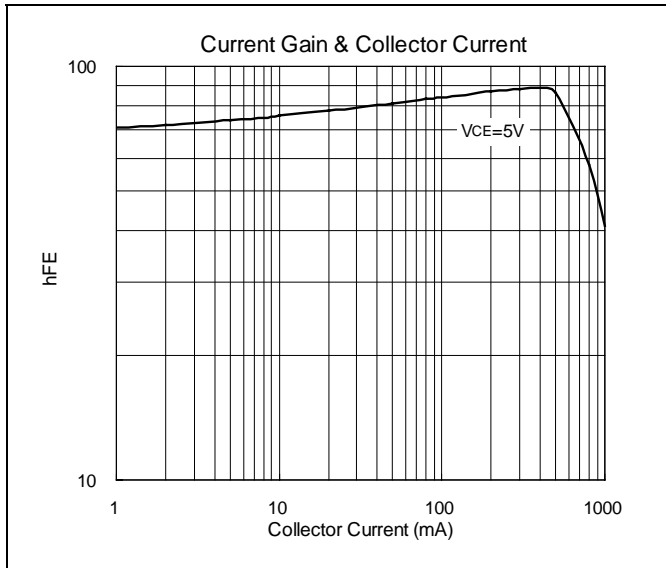
*Pulse Test: Pulse Width ≤380us, Duty Cycle≤2%

Classification Of hFE1

Rank	B	C	D
Range	60-120	100-200	180-320

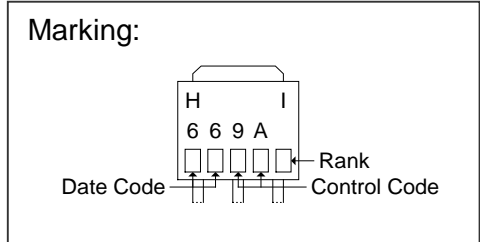
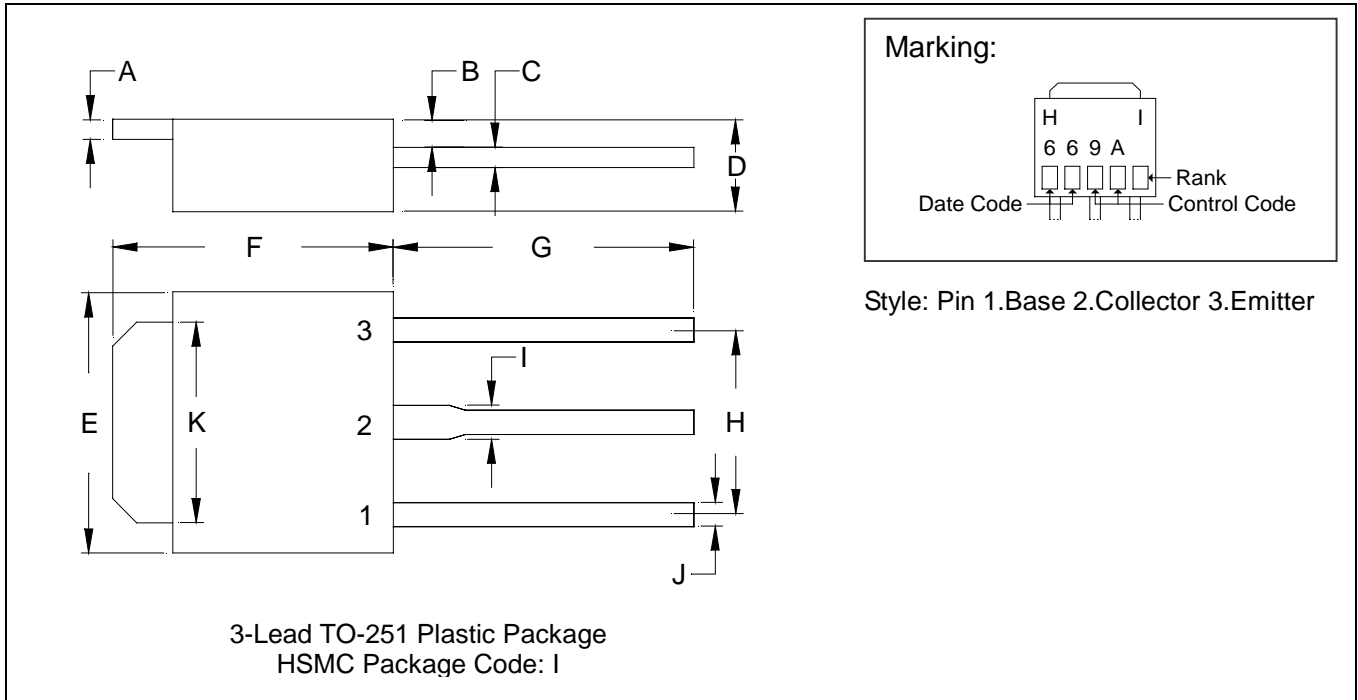


Characteristics Curve





TO-251 Dimension



Style: Pin 1.Base 2.Collector 3.Emitter

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0177	0.0217	0.45	0.55	G	0.2559	-	6.50	-
B	0.0354	0.0591	0.90	1.50	H	-	*0.1811	-	*4.60
C	0.0177	0.0236	0.45	0.60	I	-	0.0354	-	0.90
D	0.0866	0.0945	2.20	2.40	J	-	0.0315	-	0.80
E	0.2520	0.2677	6.40	6.80	K	0.2047	0.2165	5.20	5.50
F	0.2677	0.2835	6.80	7.20					

- Notes: 1.Dimension and tolerance based on our Spec. dated May. 24,1995.
 2.Controlling dimension: millimeters.
 3.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 4.If there is any question with packing specification or packing method, please contact your local HSMC sales office.

Material:

- Lead: 42 Alloy; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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